



# High Power 670nm 300mW FP Laser Diode in C-Mount Package LD670E300G13

Data Sheet

## Features

- 670nm Fabry-Perot cavity semiconductor laser
- Optical output power: 300mW CW
- High output power
- No monitor photodiode
- Package: C-Mount

## Specifications (T<sub>c</sub> = 20°C)

### Optical Characteristics

PARAMETER	MIN.	TYP.	MAX.	UNIT
Lasing wavelength	660	670	680	nm
Output power	-	300	-	mW
Spectral width	-	1.0	2.0	nm
Emitting area width	-	100	-	um
Temperature coefficient	-	0.30	-	nm/°C
Fast axis divergence	-	34	38	deg
Slow axis divergence	-	7	10	deg

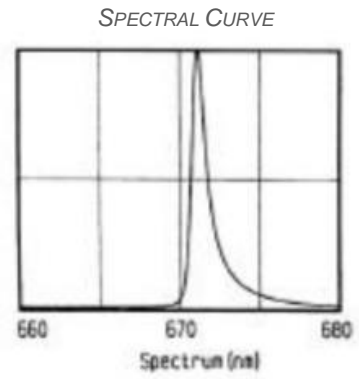
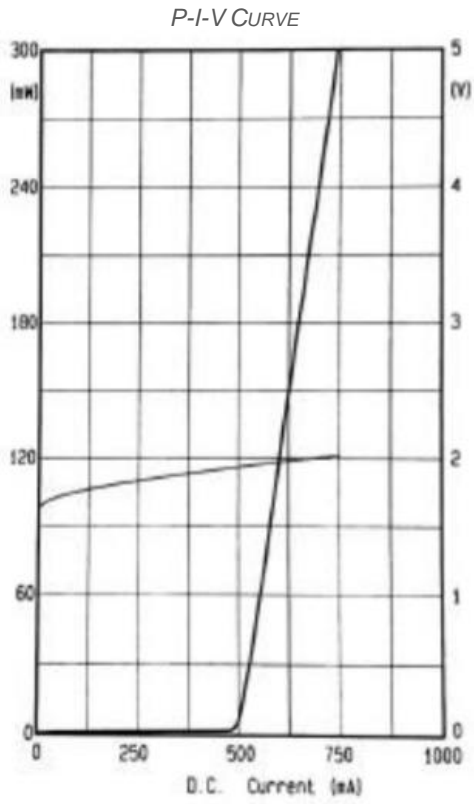
### Electrical Characteristics

PARAMETER	MIN.	TYP.	MAX.	UNIT
Slope efficiency	0.90	-	-	W/A
Threshold current	-	0.50	0.60	A
Operating current	-	0.80	1.00	A
Operating voltage	-	2.00	2.30	V

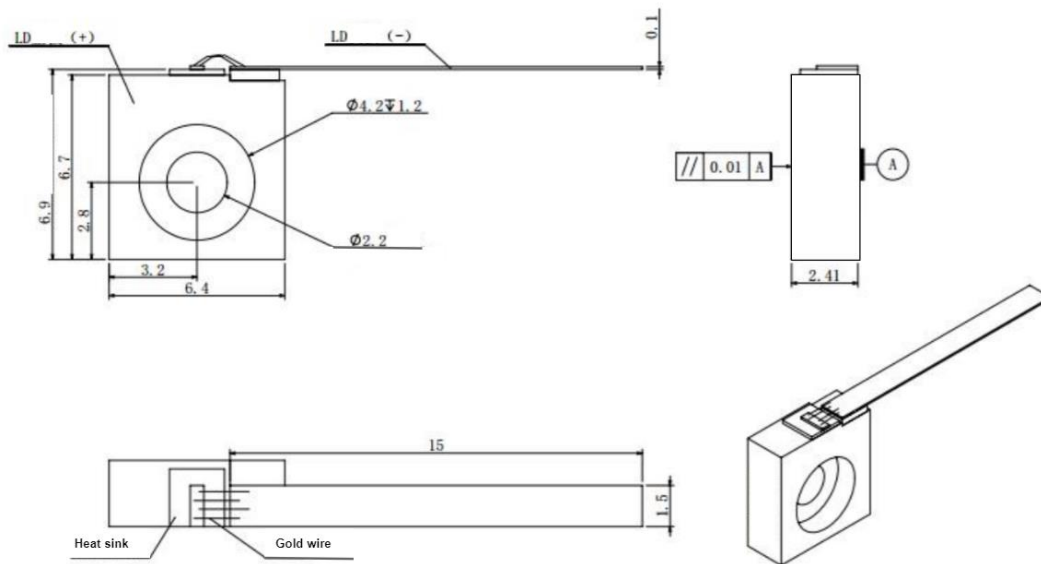
### Other Characteristics

PARAMETER	MIN.	TYP.	MAX.	UNIT
Package		C-Mount		-
Operating temperature	10		30	°C
Storage temperature	-10		60	°C

Typical Characteristics



Mechanical Outline (unit: mm)



**Additional Notes**

- Do not operate the device above maximum ratings. Doing so may cause unexpected and permanent damage to the device.
- Take precautions to avoid electrostatic discharge and/or momentary power spikes. A change in the characteristics of the laser or premature failure may result.
- Proper heat sinking of the device assures stability and lifetime. Always ensure that maximum operating temperatures are not exceeded.
- Observing visible or invisible laser beams with human eye directly, or indirectly, can cause permanent damage. Use a camera to observe the laser.
- No laser device should be used in any application or situation where life or property is at risk in the event of device failure.
- Specifications are subject to change without notice. Ensure that you have the latest specification by contacting us prior to purchase or use of the product.